

Data sheet acquired from Harris Semiconductor SCHS273

August 1997

High Speed CMOS Logic Triple 3-Input AND Gate

Features

- · Buffered Inputs
- Typical Propagation Delay: 8ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C
- Fanout (Over Temperature Range)
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility,
 V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, I_I \leq 1 μ A at V_{OL}, V_{OH}

Description

The Harris CD54HCT11, CD74HC11, and CD74HCT11 logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 74HCT logic family is functionally pin compatible with the standard 74LS logic family.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC11E	-55 to 125	14 Ld PDIP	E14.3
CD74HCT11E	-55 to 125	14 Ld PDIP	E14.3
CD74HC11M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT11M	-55 to 125	14 Ld SOIC	M14.15
CD54HCT11F	-55 to 125	14 Ld CERDIP	F14.3

NOTES:

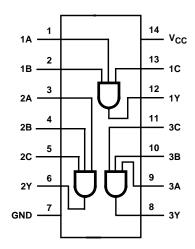
- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

CD54HCT11, CD74HC11, CD74HCT11 (PDIP, CERDIP, SOIC) TOP VIEW

1A 1 14 VCC
1B 2 13 1C
2A 3 12 1Y
2B 4 11 3C
2C 5 10 3B
2Y 6 9 3A
GND 7 8 3Y

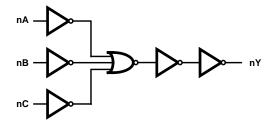
Functional Diagram



TRUTH TABLE

INP	UTS		OUTPUT
nA	nB	nC	nY
L	L	L	L
L	L	Н	L
L	Н	L	L
L	Н	Н	L
Н	L	L	L
Н	L	Н	L
Н	Н	L	L
Н	Н	Н	Н

Logic Symbol



Absolute Maximum Ratings

DC Supply Voltage, V _{CC} 0.8	5V to 7V
DC Input Diode Current, I _{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$.±20mA
DC Output Diode Current, IOK	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$.±20mA
DC Output Source or Sink Current per Output Pin, IO	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$.±25mA
DC V _{CC} or Ground Current, I _{CC or} I _{GND}	.±50mA

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)	θ_{JC} ($^{o}C/W$)
PDIP Package	100	N/A
CERDIP Package	130	55
SOIC Package	180	N/A
Maximum Junction Temperature (Hermetic I	Package or Di	e) 175 ⁰ C
Maximum Junction Temperature (Plastic F	Package)	150 ^o C
Maximum Storage Temperature Range	65	^o C to 150 ^o C
Maximum Lead Temperature (Soldering 1	0s)	300°C
(SOIC - Lead Tips Only)		

Operating Conditions

Temperature Range (T _A)
Supply Voltage Range, V _{CC}
HC Types2V to 6V
HCT Types
DC Input or Output Voltage, V _I , V _O 0V to V _{CC}
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. $\theta_{\mbox{\scriptsize JA}}$ is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

			ST ITIONS		25°C			-40°C T	O 85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES												
High Level Input	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	٧
				6	4.2	i	-	4.2	-	4.2	-	V
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	٧
				6	ı	i	1.8	i	1.8	-	1.8	V
High Level Output	V _{OH}	V _{IH} or	-0.02	2	1.9	-	-	1.9	-	1.9	-	٧
Voltage CMOS Loads		V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	٧
			-0.02	6	5.9	-	-	5.9	-	5.9	-	٧
High Level Output			-	-	1	-	-	-	-	-	-	٧
Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	٧
			-5.2	6	5.48	i	-	5.34	-	5.2	-	V
Low Level Output	V _{OL}	V _{IH} or	0.02	2	1	-	0.1	-	0.1	-	0.1	٧
Voltage		V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	٧
			0.02	6	-	-	0.1	-	0.1	-	0.1	٧
Low Level Output			-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			4	4.5	-	-	0.26	i	0.33	-	0.4	V
			5.2	6	1	1	0.26	i	0.33	-	0.4	V
Input Leakage Current	lı	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μА

DC Electrical Specifications (Continued)

			ST ITIONS		25°C			-40°C TO 85°C			-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS	
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	2	-	20	-	40	μА	
HCT TYPES													
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V	
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V	
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V	
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V	
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V	
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V	
Input Leakage Current	I _I	V _{CC} and GND	-	5.5	-		±0.1	-	±1	-	±1	μА	
Quiescent Device Current	Icc	V _{CC} or GND	-	5.5	-	-	2	-	20	-	40	μА	
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	Δl _{CC}	V _{CC} - 2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μА	

NOTE:

HCT Input Loading Table

INPUT	UNIT LOADS						
All	0.5						

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g. 360 μA max at 25°C.

Switching Specifications Input t_r , t_f = 6ns

		TEST	TEST	v _{cc}		25°C		-40°C T	O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS	
HC TYPES									-			
Propagation Delay, Input to Output (Figure 1)	t _{PLH} , t _{PHL}	C _L = 50pF	2	ı	-	100	-	125	-	150	ns	
			4.5	-	-	20	-	25	-	30	ns	
			6	-	-	17	-	21	-	26	ns	
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	8	-	-	-	-	-	ns	

^{4.} For dual-supply systems theorectical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

Switching Specifications Input t_r , t_f = 6ns (Continued)

		TEST	v _{cc}		25°C		-40°C T	O 85°C	-55°C T	O 125 ⁰ C	
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	Cl	C _L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	C _L = 15pF	5	-	26	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 2)	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	-	28	ı	35	-	42	ns
Propagation Delay, Data Input to Output Y	t _{PLH} , t _{PHL}	C _L = 15pF	5	-	11	-	-	-	-	-	ns
Transition Times (Figure 2)	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C _I	C _L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	-	5	-	28	i	-	1	-	-	pF

NOTES:

- 5. $C_{\mbox{\scriptsize PD}}$ is used to determine the dynamic power consumption, per gate.
- 6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Test Circuits and Waveforms

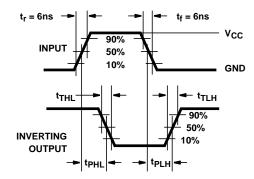


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

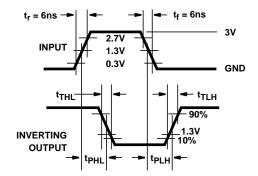


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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